

5th Generation CoolSiC™ 1200V Schottky Diode

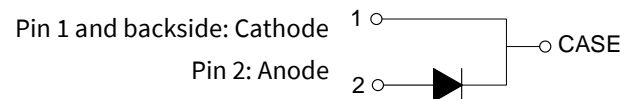
SiC Diode

Features

- Revolutionary semiconductor material - Silicon Carbide
- No reverse recovery current / no forward recovery
- Temperature independent switching behaviour
- Low forward voltage even at high operating temperature
- Tight forward voltage distribution
- Excellent thermal performance
- Extended surge current capability
- Specified dv/dt ruggedness
- Pb-free lead plating; RoHS compliant



Pin definition



Potential applications

- Drives
- Industrial power supplies: Industrial UPS
- Solar central inverters and Solar string inverter

Product validation

- Qualified for industrial applications according to the relevant tests of JEDEC 47/20/22

Description

- System efficiency improvement over Si diodes
- Enabling higher frequency / increased power density solutions
- System size/cost savings due to reduced heatsink requirements and smaller magnetics
- Reduced EMI
- Highest efficiency across the entire load range
- Robust diode operation during surge events
- High reliability
- Related Links: www.infineon.com/SiC



Key performance parameters

Type	V_{DC}	I_F	Q_c	$T_{vj,max}$	Marking	Package
IDK05G120C5	1200 V	5 A	24nC	175°C	D0512C5	PG-TO263-2



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Maximum ratings

1 Maximum ratings

Note: For optimum lifetime and reliability, Infineon recommends operating conditions that do not exceed 80% of the maximum ratings stated in this datasheet.

Parameter	Symbol	Value	Unit
Repetitive peak reverse voltage $T_C \geq 25^\circ\text{C}$	V_{RRM}	1200	V
Continuous forward current for $R_{th(j-c,max)}$ $T_C = 161^\circ\text{C}, D=1$ $T_C = 135^\circ\text{C}, D=1$ $T_C = 25^\circ\text{C}, D=1$	I_F	5.0 9.2 19.1	A
Surge repetitive forward current, sine halfwave ¹ $T_C=25^\circ\text{C}, t_p=10\text{ms}$ $T_C=100^\circ\text{C}, t_p=10\text{ms}$	$I_{F,RM}$	20 15	A
Surge non-repetitive forward current, sine halfwave $T_C=25^\circ\text{C}, t_p=10\text{ms}$ $T_C=150^\circ\text{C}, t_p=10\text{ms}$	$I_{F,SM}$	59 50	A
Non-repetitive peak forward current $T_C = 25^\circ\text{C}, t_p=10 \mu\text{s}$	$I_{F,max}$	472	A
i^2t value $T_C = 25^\circ\text{C}, t_p=10 \text{ms}$ $T_C = 150^\circ\text{C}, t_p=10 \text{ms}$	$\int i^2 dt$	17.4 12.5	A^2s
Diode dv/dt ruggedness $V_R=0\dots960 \text{V}$	dv/dt	80	V/ns
Power dissipation for $R_{th(j-c,max)}$ $T_C = 25^\circ\text{C}$	P_{tot}	109	W

¹ Not subject to production test. The test was performed with 20000 pulses (two consecutive half-wave rectified sines with 10 ms period).

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SiC Diode



Maximum ratings

Operating temperature	T_{vj}	-55...175	°C
Storage temperature	T_{stg}	-55...150	°C
Soldering temperature, reflow soldering (MSL1 according to JEDEC J-STD-020)	T_{sold}	260	°C

Thermal resistances

2 Thermal resistances

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Characteristic						
Diode thermal resistance, junction – case	$R_{th(j-c)}$		-	1.06	1.37	K/W
Thermal resistance, junction – ambient	$R_{th(j-a)}$	Leaded	-	-	62	K/W

3 Electrical Characteristics

Static Characteristics, at $T_{vj}=25^{\circ}\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
DC blocking voltage	V_{DC}	$T_{vj} = 25^{\circ}\text{C}, I_R=50\mu\text{A}$	1200	-	-	V
Diode forward voltage	V_F	$I_F=5\text{A}, T_{vj}=25^{\circ}\text{C}$	-	1.50	1.8	V
		$I_F=5\text{A}, T_{vj}=150^{\circ}\text{C}$	-	1.95	-	
Reverse current	I_R	$V_R=1200\text{V}, T_{vj}=25^{\circ}\text{C}$	-	2.5	33	μA
		$V_R=1200\text{V}, T_{vj}=150^{\circ}\text{C}$	-	12	-	

Dynamic Characteristics, at $T_{vj}=25^{\circ}\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Total capacitive charge	Q_C	$V_R=800\text{V}, T_{vj}=150^{\circ}\text{C}$	-	24	-	nC
		$Q_C = \int_0^{V_R} C(V)dV$				
Total Capacitance	C	$V_R=1\text{V}, f=1\text{MHz}$	-	301	-	pF
		$V_R=400\text{V}, f=1\text{MHz}$	-	21	-	
		$V_R=800\text{V}, f=1\text{MHz}$	-	17	-	

4 Electrical Characteristics Diagrams

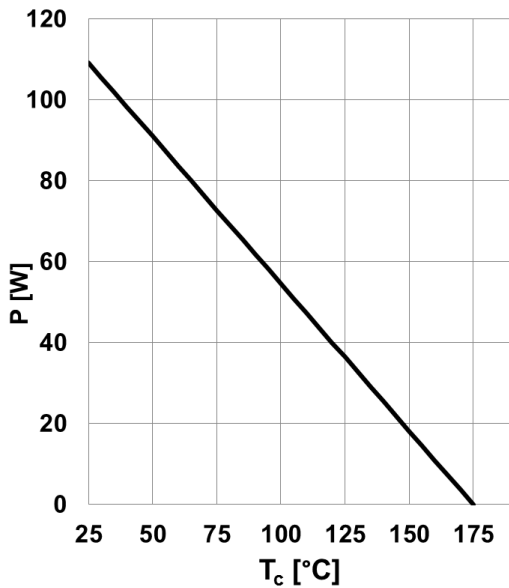


Figure 1. Power dissipation as function of case temperature, $P_{tot}=f(T_c)$, $R_{th(j-c),max}$

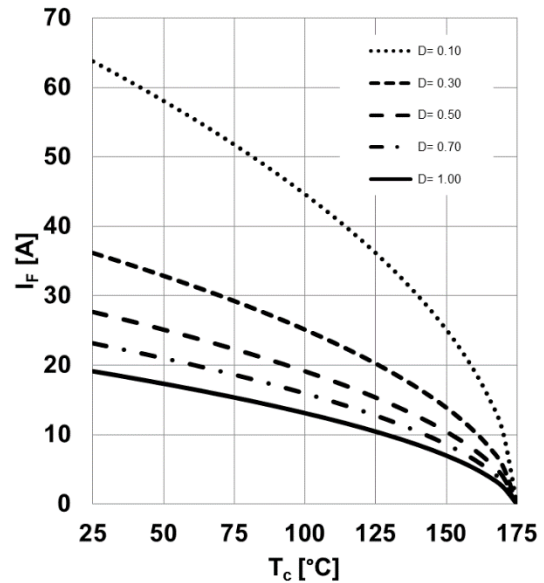


Figure 2. Diode forward current as function of temperature, parameter: $T_{vj} \leq 175^\circ\text{C}$, $R_{th(j-c),max}$, D =duty cycle, V_{th} , R_{diff} @ $T_{vj}=175^\circ\text{C}$

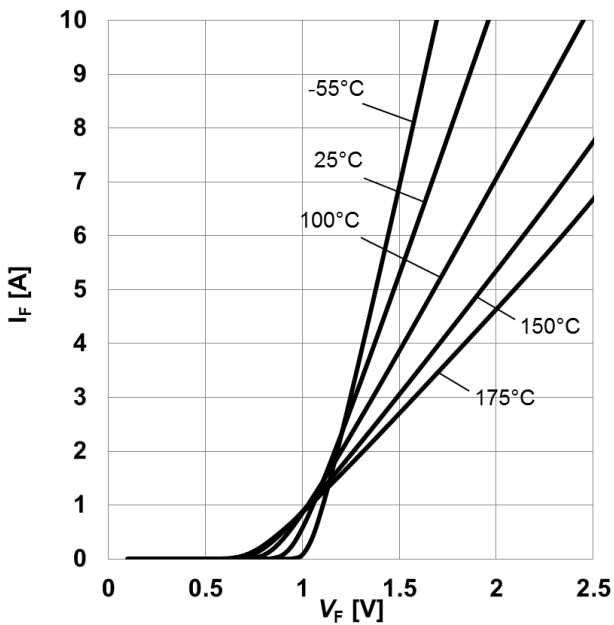


Figure 3. Typical forward characteristics, $I_F=f(V_F)$, $t_p=10 \mu\text{s}$, parameter: T_{vj}

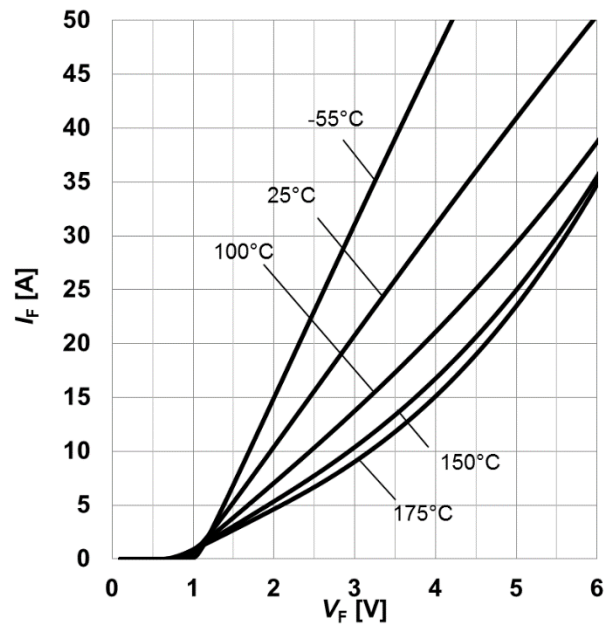


Figure 4. Typical forward characteristics in surge current, $I_F=f(V_F)$, $t_p=10 \mu\text{s}$, parameter: T_{vj}

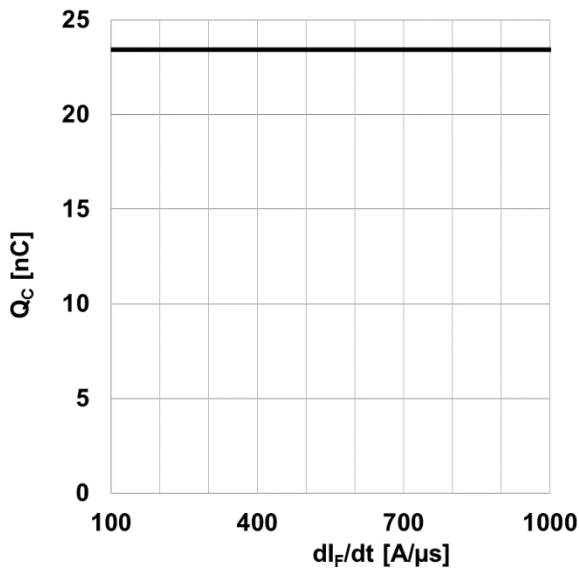


Figure 5. Typical capacitive charge as function of current slope, $Q_c=f(dI_F/dt)$, $T_{vj}=150^{\circ}\text{C}$

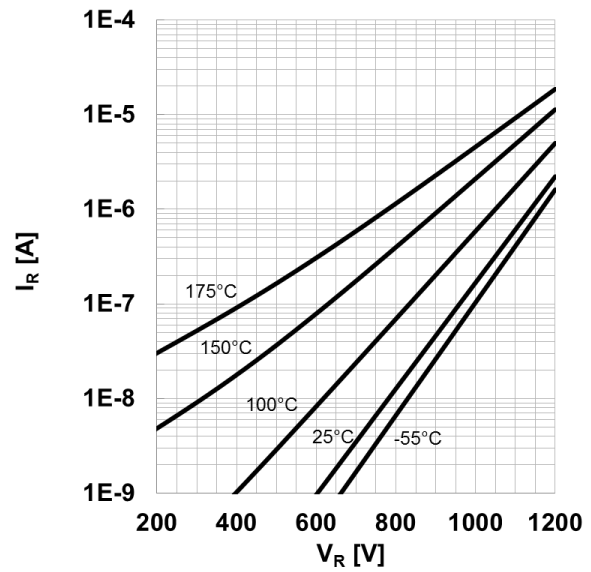


Figure 6. Typical reverse characteristics, $I_R=f(V_R)$, parameter: T_{vj}

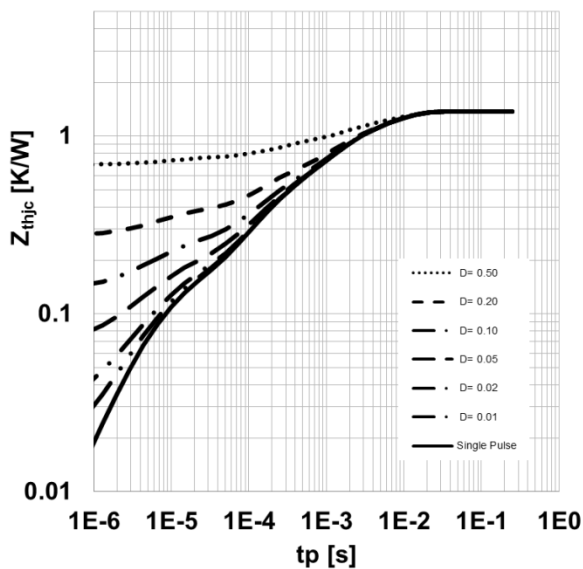


Figure 7. Max. transient thermal impedance, $Z_{th,j-c}=f(t_p)$, parameter: $D=t_p/T$

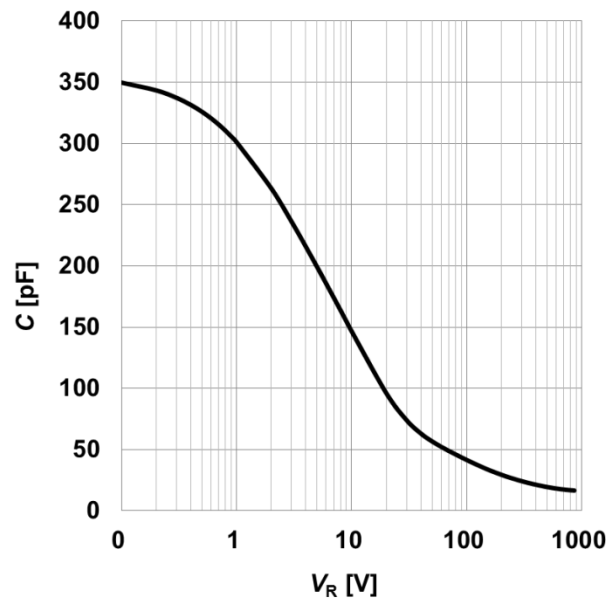


Figure 8. Typical capacitance as function of reverse voltage, $C=f(V_R)$; $T_{vj}=25^{\circ}\text{C}$; $f=1\text{ MHz}$

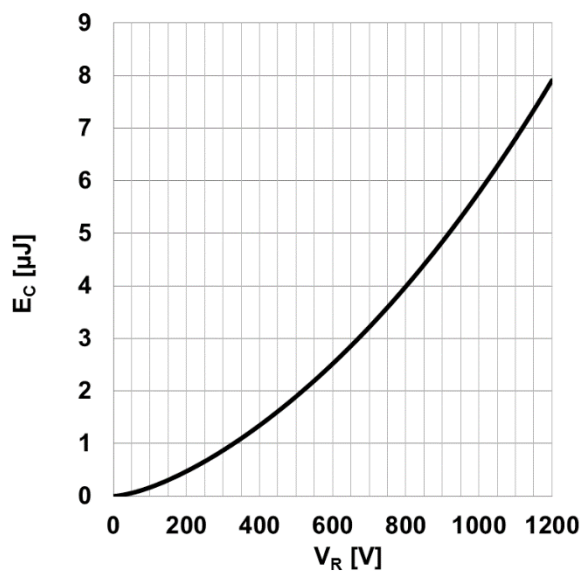
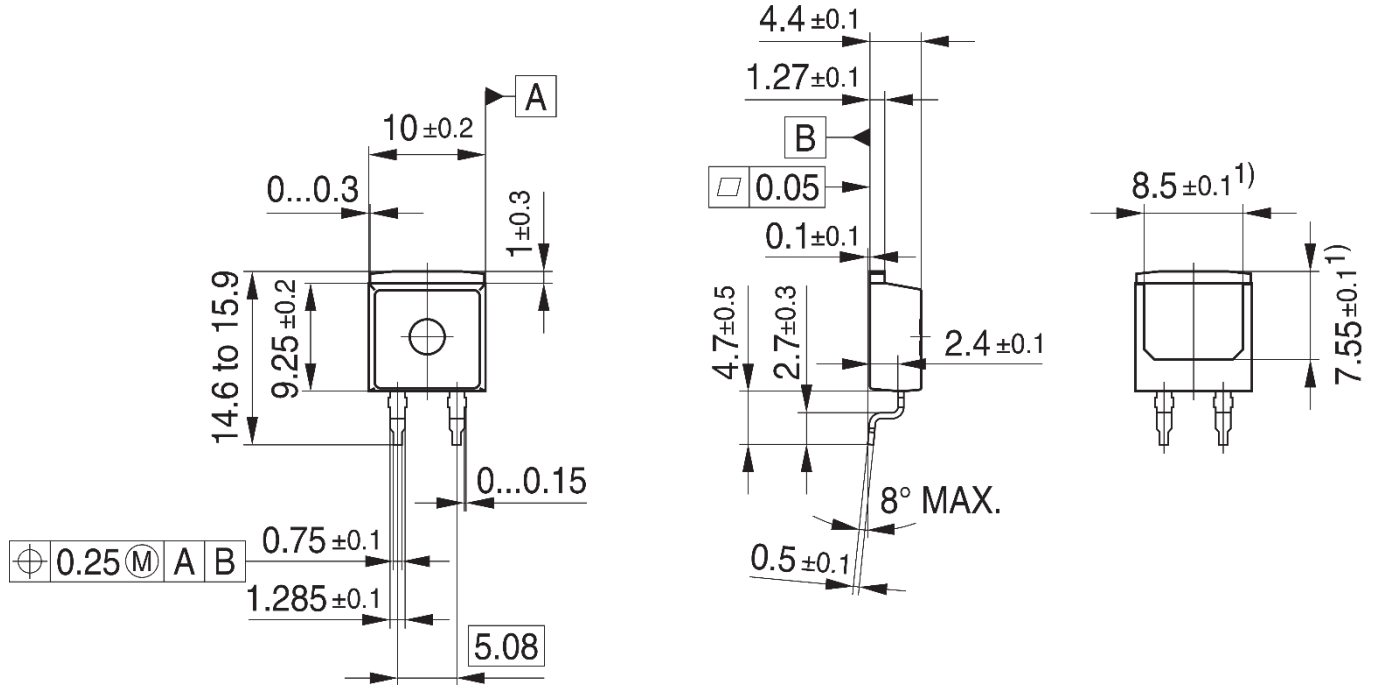


Figure 9. Typical capacitively stored energy as function of reverse voltage, $E_C=f(V_R)$

5 Package Drawing

PG-T0263-2



- 1) Typical
 Metal surface min. X = 7.25, y = 6.9
 All metal surfaces: tin plated, except area of cut

All dimensions do not include mold flash or protrusions
 All dimensions are in units mm
 The drawings is in compliance with ISO 128-30, Projection Method 1 [⊕]

Revision history

Revision history

Document version	Date of release	Description of changes
V 1.0	2019-01-25	Preliminary Datasheet
V 2.0	2019-10-28	Final Datasheet

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